NSN 5962-01-408-0767

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Maximum Power Dissipation Rating:

330.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Milstar

Features Provided:

Burn in, mil-std-883, class b and electrostatic sensitive and monolithic and programmed and radiation hardened and tested to mil-std-883 and ultraviolet erasable and w/enable

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

27 input

Criticality Code Justification:

Cbbl

Current Rating Per Characteristic:

1.00 milliamperes reverse current, dc blank and 10.00 microamperes reverse current, dc microamperes

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, digital, memory (hci)

Voltage Rating And Type Per Characteristic:

-0.6 volts power source and 7.0 volts power source

Capitance Rating Per Characteristic:

12.00 input picofarads and 15.00 output picofarads

Time Rating Per Chacteristic:

200.00 nanoseconds delay

Memory Device Type:

Prom

Special Features:

Device is a 512k x 8 cmos uveprom; this is an altered item made from rc258-0249-010 which is selected from 258-0249-010 which is a 67268 5962-9175202mxa (27c040); case outline designator cdip2-t32 or gdip1-t32 as designated in mil-std-1835

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

32 printed circuit

Shelf Life:

N/a

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Demilitarization:

No

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